IN THE SPECIFICATION:

Page 15, line 9, please amend the following paragraph as follows:

The properties of protective layer 15 related to suppressing discharge variability are exhibited by fine MgO crystalline particles 15B, whose very pure crystal structure results in excellent electron emission properties. Specifically, as shown in the Fig.5 energy band diagram of the protective layer, firstly VUV following on from the electric field generated in discharge spaces 24 when PDP 1 is driven causes electrons in fine MgO crystalline particles 15B to migrate to oxygen deficient regions. The oxygen deficient regions then act as the luminescence center owing to the energy difference (E2 – E1) between electrons in these regions, and emit visible light. Following the visible light emission, electrons in fine MgO crystalline particles 15B are excited from the valence band Ev to an energy level (impurity level E3) in a vicinity of the conduction band Ec. The carrier density of protective layer 15 improves with the increase in electrons having impurity level E3, allowing for impedance control. Black noise can thus be prevented in addition to controlling discharge variability when PDP 1 is driven, improving the discharge probability of the PDP. Since the properties of protective layer 15 related to suppressing discharge variability are similar to those achieved with carrier doping in semiconductors, high crystallinity (few impurities, excellent orientability, etc.) is demanded of protective layer 15 in order to realize these properties. In view of this, embodiment 1, in order to achieve excellent suppression of discharge variability, uses fine MgO crystalline particles 15B having excellent electron emission properties (i.e. high crystallinity), and assigns these particles with the task of suppressing discharge variability to prevent black noise. In fine MgO crystalline particles 15B, so as to obtain a large number of oxygen-depleted regions, an oxygen rich composition is used.

Page 19, line 11, please amend the following paragraph as follows:

On the other hand, using a photomask technique, with a metal (Ag) powder and an organic vehicle is mixed a photosensitive resin. This is applied over the transparent electrode material and covered with a mask having the pattern of the display electrodes. The mask is then exposed from above and developed/baked (baking temp. of approx. 590°C - 600°C). Buslines are thus formed on the transparent electrodes. This photomask technique enables the width of the buslines to be reduced to approximately 30 μm, in comparison with conventional screen-printing techniques whose minimum width is 100 μm. Note that materials other than Ag can be used in the buslines, examples of which include platinum (Pt), gold (Au), Al, nickel (Ni), Cr, tin oxide, and indium oxide.

Page 23, line 25, please delete the following paragraph:

~~In embodiment 1, as protective layer 15, MgO crystal 15A.~~